ESD Protection Diode Array

Quad, Low Capacitance

This integrated surge protection device is designed for applications requiring transient overvoltage protection. It is intended to be used in sensitive equipment such as wireless headsets, PDAs, digital cameras, computers, printers, communication systems, and other applications. The integrated design provides very effective and reliable protection for four separate lines using only one package. This device is ideal for situations where board space is at a premium.

Features

- ESD Protection: IEC61000-4-2: Level 4
- Four Separate Unidirectional Configurations for Protection
- Low Leakage Current < 1 μA @ 3 V
- Small SOT-953 SMT Package
- Low Capacitance
- This is a Pb-Free Device

Benefits

- Provides Protection for ESD Industry Standards: IEC 61000, HBM
- Protects Four Lines Against Transient Voltage Conditions
- Minimize Power Consumption of the System
- Minimize PCB Board Space

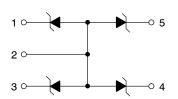
Typical Applications

- Cellular and Portable Electronics
- Serial and Parallel Ports
- Microprocessor Based Equipment
- Notebooks, Desktops, Servers



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SOT-953 CASE 526AE

MARKING DIAGRAM



6 = Specific Device Code

M = Date Code

ORDERING INFORMATION

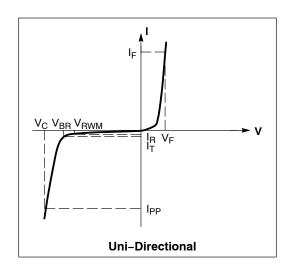
Device	Package	Shipping [†]		
NUP46V8P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ IPP		
V _{RWM} Working Peak Reverse Voltage			
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
Ι _Τ	Test Current		
ΘV _{BR}	Maximum Temperature Coefficient of V _{BR}		
I _F	Forward Current		
V _F	Forward Voltage @ I _F		
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}		
I _{ZK}	Reverse Current		
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}		



MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ T _A = 25°C) (Note 1)	P _{PK}	10	W
Thermal Resistance Junction-to-Ambient Above 25°C, Derate	$R_{ hetaJA}$	560 4.5	°C/W mW/°C
Maximum Junction Temperature	T _{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T _J T _{stg}	-55 to +150	°C
Lead Solder Temperature (10 seconds duration)	TL	260	°C
Human Body Model (HBM) Machine Model (MM)	ESD	8000 400	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS $(T_A = 25^{\circ}C)$

	Device	Breakdown Voltage V _{BR} @ 1 mA (Volts)		Leakage Current I _{RM} @ V _{RM}		Typ Capacitance @ 0 V Bias (pF) (Note 2)		Typ Capacitance @ 3 V Bias (pF) (Note 2)		
Device	Marking	Min	Nom	Max	V _{RWM}	I _{RWM} (μA)	Тур	Max	Тур	Max
NUP46V8P5	6	6.47	6.8	7.14	4.3	1.0	12	15	6.7	9.5

Non-repetitive current per Figure 1.
 Capacitance of one diode at f = 1 MHz, V_R = 0 V, T_A = 25°C.

TYPICAL ELECTRICAL CHARACTERISTICS

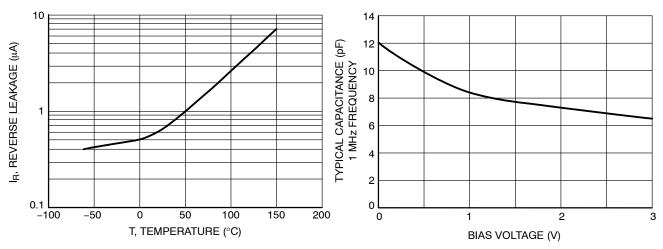


Figure 1. Reverse Leakage versus Temperature

Figure 2. Capacitance

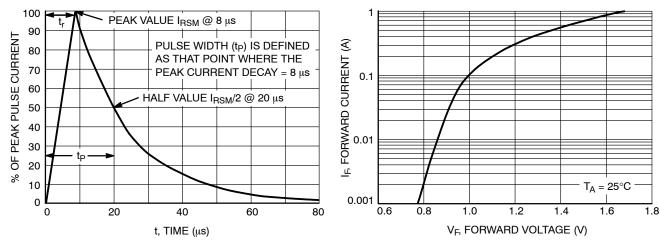


Figure 3. $8\times20~\mu s$ Pulse Waveform

Figure 4. Forward Voltage

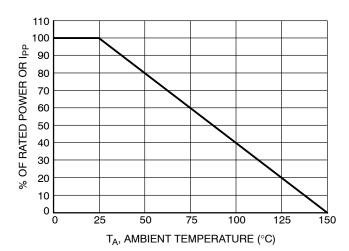
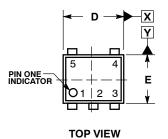
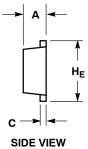


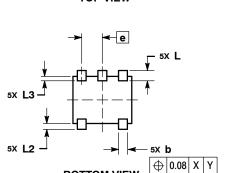
Figure 5. Power Derating Curve

PACKAGE DIMENSIONS

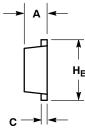
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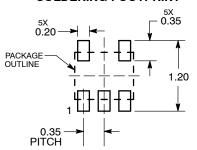
BOTTOM VIEW



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS							
DIM	MIN	MIN NOM MA						
Α	0.34	0.37	0.40					
b	0.10	0.15 0.2						
С	0.07	0.12	0.17					
D	0.95	1.00	1.05					
Е	0.75	0.80	0.85					
е	0.35 BSC							
HE	0.95	1.00	1.05					
L	0.175 REF							
L2	0.05	0.10 0.15						
13			0.15					

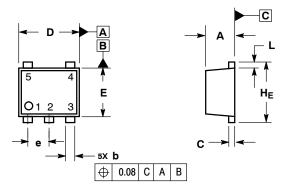
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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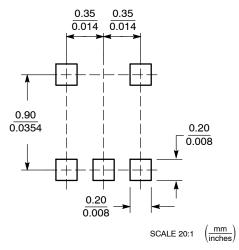


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 2. GON HOLLING DIMENSION. MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
 FINISH THICKNESS. MINIMUM LEAD THICKNESS
 IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.34	0.37	0.40				
b	0.10	0.15	0.20	0.004	0.006	0.008	
C	0.07	0.12	0.17	0.003	0.005	0.007	
D	0.95	1.00	1.05	0.037	0.039	0.041	
Е	0.75	0.80	0.85	0.03	0.032	0.034	
е	0.35 BSC			0.014 BSC			
Ь	0.05	0.10	0.15	0.002	0.004	0.006	
HE	0.95	1.00	1.05	0.037	0.039	0.041	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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